Valeria VadalÃ

List of Publications by Year
in descending order

55	720	567281 15	552781 26
papers	citations	h-index	g-index

55	55	55	353
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Nonlinear Dispersive Modeling of Electron Devices Oriented to GaN Power Amplifier Design. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 710-718.	4.6	99
2	Behavioral Modeling of GaN FETs: A Load-Line Approach. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 73-82.	4.6	67
3	Characterization of GaN HEMT Low-Frequency Dispersion Through a Multiharmonic Measurement System. IEEE Transactions on Microwave Theory and Techniques, 2010, 58, 2490-2496.	4.6	62
4	A Loadâ€“Pull Characterization Technique Accounting for Harmonic Tuning. IEEE Transactions on Microwave Theory and Techniques, 2013, 61, 2695-2704.	4.6	50
5	X-Band GaN Power Amplifier for Future Generation SAR Systems. IEEE Microwave and Wireless Components Letters, 2014, 24, 266-268.	3.2	43
6	Empowering GaN HEMT models: The gateway for power amplifier design. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2017, 30, e2125.	1.9	40
7	Accurate GaN HEMT nonquasiâ€static largeâ€signal model including dispersive effects. Microwave and Optical Technology Letters, 2011, 53, 692-697.	1.4	33
8	Millimeter-Wave FET Nonlinear Modelling Based on the Dynamic-Bias Measurement Technique. IEEE Transactions on Microwave Theory and Techniques, 2014, 62, 2526-2537.	4.6	29
9	High-periphery GaN HEMT modeling up to 65â€GHz and 200â€Â°C. Solid-State Electronics, 2019, 152, 11-16.	1.4	24
10	A New Modeling Technique for Microwave Multicell Transistors Based on EM Simulations. IEEE Transactions on Microwave Theory and Techniques, 2020, 68, 3100-3110.	4.6	20
11	Dynamic-Bias S-Parameters: A New Measurement Technique for Microwave Transistors. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 3946-3955.	4.6	18
12	Nonlinear-Embedding Design Methodology Oriented to LDMOS Power Amplifiers. IEEE Transactions on Power Electronics, 2018, 33, 8764-8774.	7.9	18
13	Technology-Independent Analysis of the Double Current-Gain Peak in Millimeter-Wave FETs. IEEE Microwave and Wireless Components Letters, 2018, 28, 326-328.	3.2	18
14	Nonlinear embedding and deâ€embedding techniques for largeâ€signal fet measurements. Microwave and Optical Technology Letters, 2012, 54, 2835-2838.	1.4	16
15	A New Study on the Temperature and Bias Dependence of the Kink Effects in S22 and h21 for the GaN HEMT Technology. Electronics (Switzerland), 2018, 7, 353.	3.1	16
16	Nonlinear modeling of LDMOS transistors for highâ€power FM transmitters. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2014, 27, 780-791.	1.9	13
17	A New Dynamic-Bias Measurement Setup for Nonlinear Transistor Model Identification. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 218-228.	4.6	13
18	Waveform engineering: State-of-the-art and future trends (invited paper). International Journal of RF and Microwave Computer-Aided Engineering, 2017, 27, e21051.	1.2	13

#	Article	IF	Citations
19	Scalability of Multifinger HEMT Performance. IEEE Microwave and Wireless Components Letters, 2020, 30, 869-872.	3.2	13
20	Extremely low-frequency measurements using an active bias tee. , 2013, , .		12
21	Assessing GaN FET Performance Degradation in Power Amplifiers for Pulsed Radar Systems. IEEE Microwave and Wireless Components Letters, 2018, 28, 1035-1037.	3.2	12
22	An Improved Transistor Modeling Methodology Exploiting the Quasi-Static Approximation. IEEE Journal of the Electron Devices Society, 2021, 9, 378-386.	2.1	10
23	On the evaluation of the high-frequency load line in active devices. International Journal of Microwave and Wireless Technologies, 2011, 3, 19-24.	1.9	9
24	A Non-Quasi-Static FET Model Extraction Procedure Using the Dynamic-Bias Technique. IEEE Microwave and Wireless Components Letters, 2015, 25, 841-843.	3.2	9
25	Evaluation of FET performance and restrictions by low-frequency measurements. , 2014, , .		6
26	Linear versus nonlinear de-embedding: Experimental investigation. , 2013, , .		5
27	Theoretical consideration on harmonic manipulated amplifiers based on experimental data. , 2015, , .		5
28	Nonlinear model for 40-GHz cold-FET operation. , 2014, , .		4
29	A procedure for the extraction of a nonlinear microwave GaN FET model. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2017, 30, e2151.	1.9	4
30	Temperature Dependent Small-Signal Neural Modeling of High-Periphery GaN HEMTs. , 2019, , .		4
31	Analysis of Efficiency-Limiting Factors Resulting from Transistor Current Source on Class-F and Inverse Class-F Power Amplifiers. IEICE Transactions on Electronics, 2022, E105.C, 449-456.	0.6	4
32	A new empirical model for the characterization of low-frequency dispersive effects in FET electron devices accounting for thermal influence on the trapping state. , 2008, , .		3
33	GaN power amplifier design exploiting wideband large-signal matching. , 2012, , .		3
34	Thermal characterization of high-power GaN HEMTs up to 65 GHz. , 2017, , .		3
35	<scp>Equivalentâ€circuit</scp> extraction for gallium nitride electron devices: Direct versus <scp>optimizationâ€empowered</scp> approaches. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2022, 35, .	1.9	3
36	Transistor vector load-pull characterization for millimeter-wave power amplifier design. , 2012, , .		2

#	ARTICLE	IF	CITATIONS
37	GaN HEMT model extraction based on dynamic-bias measurements. , 2014, , .		2
38	A new description of fast charge-trapping effects in GaN FETs. , 2015, , .		2
39	Extraction of accurate GaN HEMT model for high-efficiency power amplifier design. , 2015, , .		2
40	Currentâ€gain in FETs beyond cutâ€off frequency. Microwave and Optical Technology Letters, 2018, 60, 3023-3026.	1.4	2
41	GaN HEMT Model with Enhanced Accuracy under Back-off Operation. , 2019, , .		2
42	A dual-source nonlinear measurement system oriented to the empirical characterization of low-frequency dispersion in microwave electron devices. Computer Standards and Interfaces, 2011, 33, 165-175.	5.4	1
43	Microwave FET model identification based on vector intermodulation measurements. , 2013, , .		1
44	Nonlinear Embedding and De-embedding. , 2014, , 385-443.		1
45	Characterization of charge-trapping effects in GaN FETs through low-frequency measurements. , 2014, , .		1
46	Nonlinear modelling of GaN transistors: Behavioural and analytical approaches. , 2015, , .		1
47	Low-frequency time-domain characterization for fast and reliable evaluation of microwave transistor performance. , 2016, , .		1
48	A streamlined drain-lag model for GaN HEMTs based on pulsed S-parameter measurements. International Journal of Microwave and Wireless Technologies, 2019, 11, 121-129.	1.9	1
49	A low-cost and accurate technique for the prediction of load-pull contours. , 2010, , .		0
50	Identification of the optimum operation for GaN HEMTs in high-power amplifiers. , 2013, , .		0
51	C-band power amplifier design based on low-frequency waveform engineering. , 2015, , .		0
52	Fast extraction of accurate I/V models for harmonically-tuned power amplifier design. , 2016, , .		0
53	75-VDC GaN technology investigation from a degradation perspective. , 2017, , .		0
54	Evaluation of high-voltage transistor reliability under nonlinear dynamic operation. , 2017, , .		0

#	Article	IF	Citations
55	Guest editorial for the special issue on modeling of <scp>Î¼mWave</scp> and <scp>mmWave</scp> electronic devices for wireless systems: Connecting technologies to applications. International Journal of Numerical Modelling: Electronic Networks, Devices and Fields, 2021, 34, e2940.	1.9	0